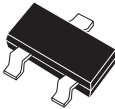


CMPT6428
CMPT6429

NPN SILICON TRANSISTOR



SOT-23 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT6428, CMPT6429 types are NPN Silicon Transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high gain amplifier applications.

Marking Codes are C1K and C1L Respectively.

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

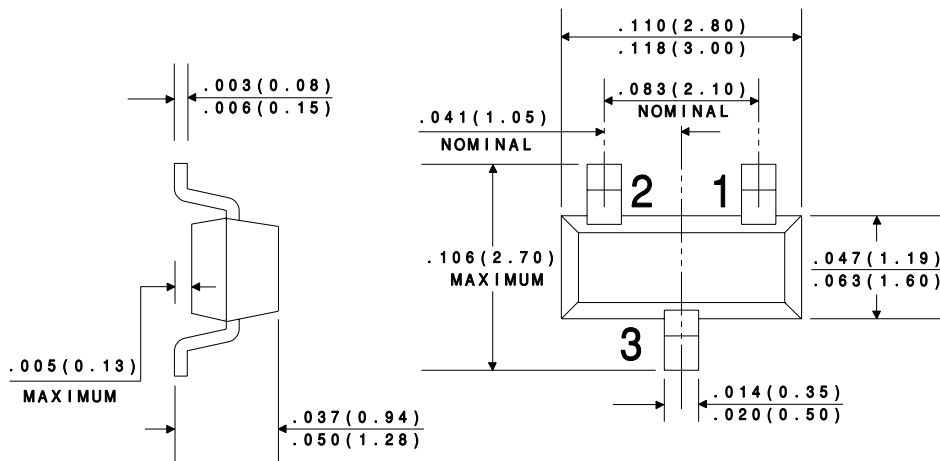
	SYMBOL	CMPT6428	CMPT6429	UNITS
Collector-Base Voltage	V_{CBO}	60	55	V
Collector-Emitter Voltage	V_{CEO}	50	45	V
Emitter-Base Voltage	V_{EBO}		6.0	V
Collector Current	I_C		200	mA
Power Dissipation	P_D		350	mW
Operating and Storage				
Junction Temperature	T_J, T_{stg}		-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}		357	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	CMPT6428		CMPT6429		UNITS
		MIN	MAX	MIN	MAX	
I_{CBO}	$V_{CB}=30\text{V}$		10		10	nA
I_{CEO}	$V_{CE}=30\text{V}$		100		100	nA
I_{EBO}	$V_{BE}=5.0\text{V}$		10		10	nA
BV_{CBO}	$I_C=100\mu\text{A}$		60		55	V
BV_{CEO}	$I_C=1.0\text{mA}$		50		45	V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=0.5\text{mA}$		0.20		0.20	V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=5.0\text{mA}$		0.60		0.60	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	0.56	0.66	0.56	0.66	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\mu\text{A}$	250		500		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=100\mu\text{A}$	250	650	500	1250	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	250		500		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	250		500		
f_T	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}, f=100\text{MHz}$	100	700	100	700	MHz

SYMBOL	TEST CONDITIONS	CMPT6428		CMPT6429		UNITS
		MIN	MAX	MIN	MAX	
C_{ob}	$V_{CB}=10V, I_E=0, f=1.0MHz$		3.0		3.0	pF
C_{ib}	$V_{BE}=0.5V, I_C=0, f=1.0MHz$		8.0		8.0	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR